



**CHENG-YI
ELECTRONIC**

BAV99W-WS

PB FREE PRODUCT

DUAL SERIES SWITCHING DIODE

Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

The BAV99W is a smaller package, equivalent to the BAV99.

Suggested Applications

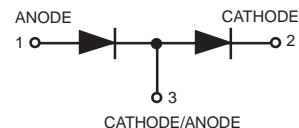
- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

DEVICE MARKING

BAV99W	A7 / KJG
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SOT-323 (SC-70)



MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (Note 1.) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-Repetitive Peak Forward Current	I_{FSM}		A
$t = 1.0 \mu s$		2.0	
$t = 1.0 \text{ ms}$		1.0	
$t = 1.0 \text{ S}$		0.5	

1. FR-5 = 1.0 × 0.75 × 0.062 in.

BAV99W

THERMAL CHARACTERISTICS

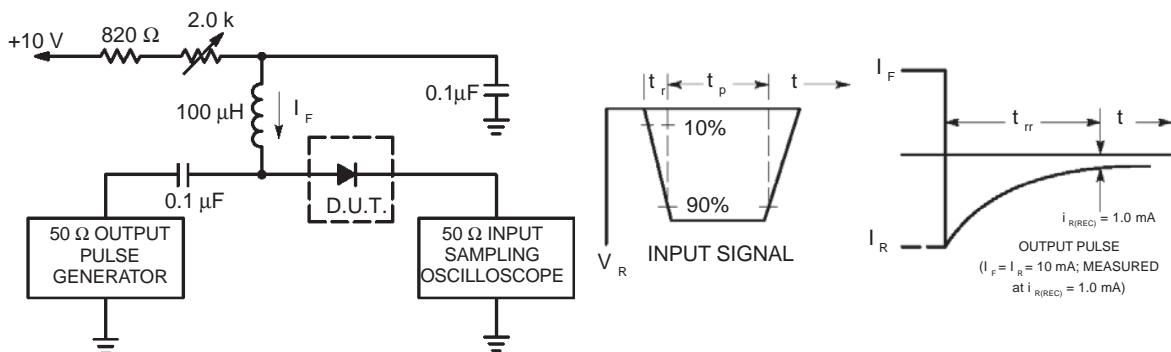
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1.) $T_A = 25^\circ\text{C}$	P_D	200	mW
Derate above 25°C		1.6	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta,JA}$	625	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2.) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	$\text{mW}/^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta,JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_{(BR)} = 100 \mu\text{A}$)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current ($V_R = 70 \text{ Vdc}$)	I_R	—	2.5	μAdc
($V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$)		—	30	
($V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$)		—	50	
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	C_D	—	1.5	pF
Forward Voltage ($I_F = 1.0 \text{ mAdc}$)	V_F	—	715	mVdc
($I_F = 10 \text{ mAdc}$)		—	855	
($I_F = 50 \text{ mAdc}$)		—	1000	
($I_F = 150 \text{ mAdc}$)		—	1250	
Reverse Recovery Time $R_L = 100 \Omega$ ($I_F = I_R = 10 \text{ mA}, i_{R(\text{REC})} = 1.0 \text{ mA}$) (Figure 1)	t_{rr}	—	6.0	ns
Forward Recovery Voltage ($I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$)	V_{FR}	—	1.75	V

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



Notes: 1. A $2.0 \text{ k}\Omega$ variable resistor adjusted for a Forward Current (I_F) of 10mA .

2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10mA .

3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAV99W

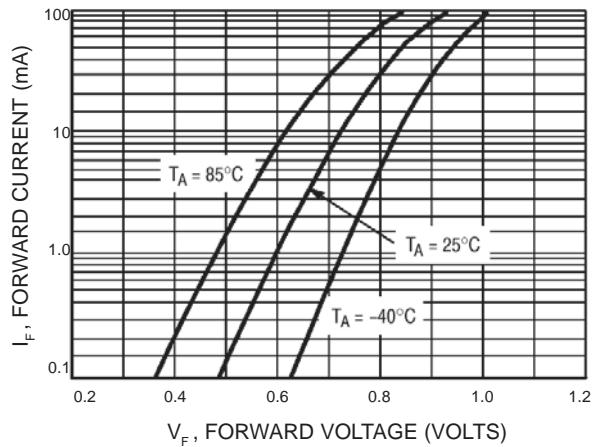


Figure 2. Forward Voltage

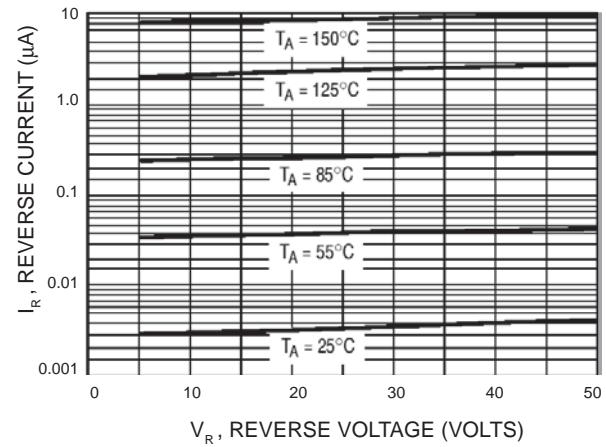


Figure 3. Leakage Current

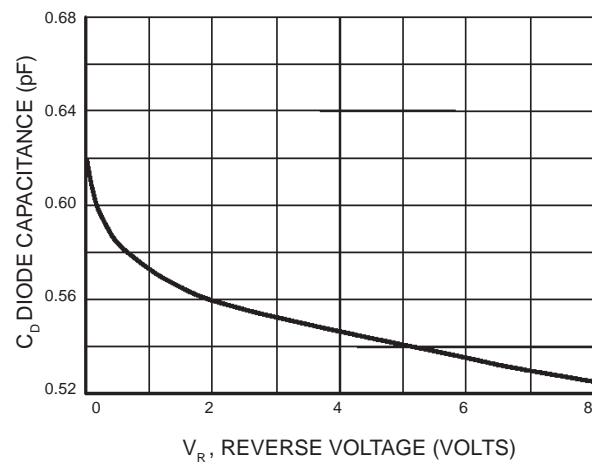


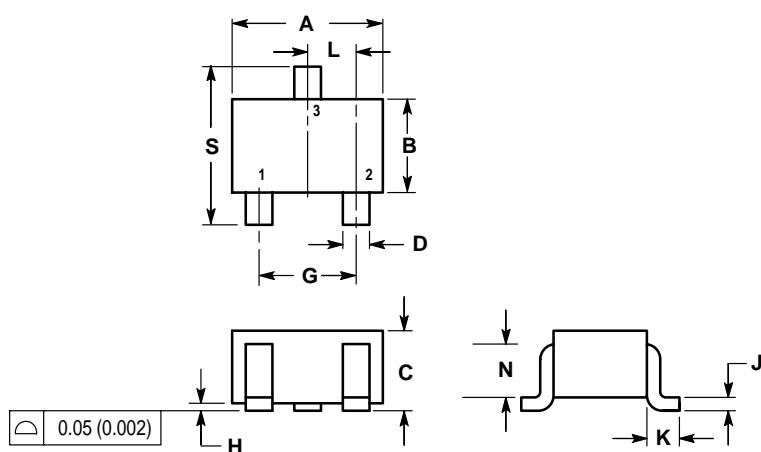
Figure 4. Capacitance

BAV90W

SC-70 / SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

